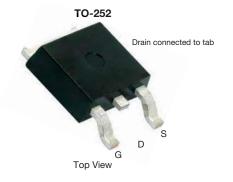


www.vishay.com

Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.013			
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.022			
I _D (A)	-50			
Configuration	Single			



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



G o —	
P-Channel MOSFET	o D

ORDERING INFORMATION			
Package	TO-252		
Lead (Pb)-free and Halogen-free	SQD50P04-13L-GE3		

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C a	1	-50	
Continuous Drain Current	T _C = 125 °C	I _D	-39	
Continuous Source Current (Diode Conduction) ^a		I _S	-50	А
Pulsed Drain Current ^b		I _{DM}	-200	
Single Pulse Avalanche Current		I _{AS}	-40	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	80	mJ
	T _A = 25 °C		3	
Maximum Power Dissipation ^b	T _C = 25 °C	P_{D}	136	W
	T _C = 125 °C		45	
Operating Junction and Storage Temperature Range		T _J , T _{sta}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-40	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-	-2.5] v
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -40 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	μΑ
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-50	-	-	Α
		V _{GS} = -10 V	I _D = -17 A	-	0.010	0.013	
Dunin Course On Otata Basistanas	_	V _{GS} = -10 V	I _D = -50 A, T _J = 125 °C	-	-	0.017	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -50 A, T _J = 175 °C	-	-	0.020	
		V _{GS} = -4.5 V	I _D = -14 A	-	0.016	0.022	
Forward Transconductance ^a	9 _{fs}	V _{DS} = -15 V, I _D = -17 A		-	61	-	S
Dynamic ^b		•					
Input Capacitance	C _{iss}			-	2872	3950	
Output Capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	508	635	pF
Reverse Transfer Capacitance	C _{rss}]		-	352	440	
Total Gate Charge ^c	Qg			-	60	80	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -30 \text{ V}, I_D = -50 \text{ A}$	-	5.7	8.6	nC
Gate-Drain Charge ^c	Q _{gd}]		-	14.7	22	
Gate Resistance	R _g	f = 1 MHz		1.5	3	4.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	15	
Rise Time ^c	t _r	$V_{DD} = -20 \text{ V}, \text{ R}_{L} = 0.4 \Omega$ $I_{D} \cong -50 \text{ A}, \text{ V}_{GEN} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	12	18]
Turn-Off Delay Time ^c	t _{d(off)}			-	40	60	ns
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	-200	Α
Forward Voltage	V _{SD}	I _F = -50 A, V _{GS} = 0 V		-	-1	-1.5	V

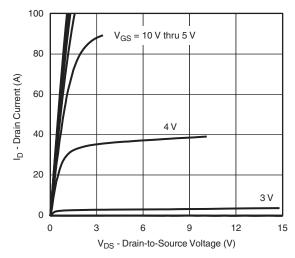
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

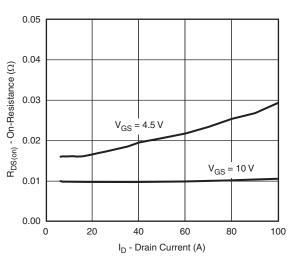
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



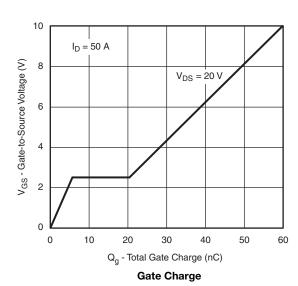
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

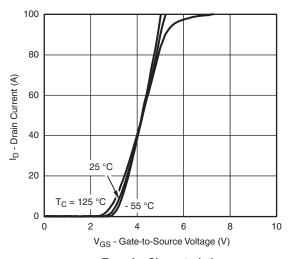


Output Characteristics

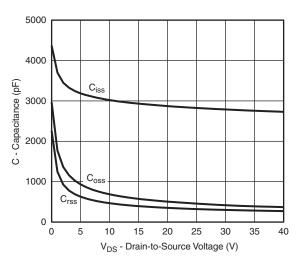


On-Resistance vs. Drain Current

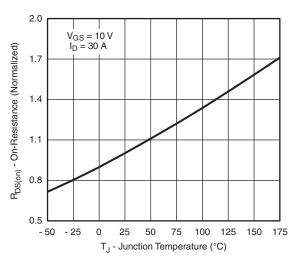




Transfer Characteristics



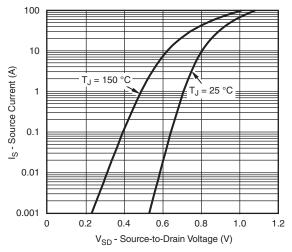
Capacitance



On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Source Drain Diode Forward Voltage

 $I_D = 250 \, \mu A$

 $I_D = 5 \text{ mA}$

150

0.8

0.5

0.2

- 0.1

- 0.4

- 50

- 25

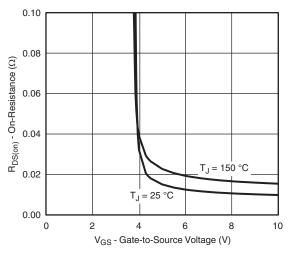
V_{GS(th)} Variance (V)



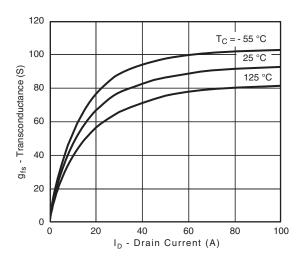
T_J - Temperature (°C)

Threshold Voltage

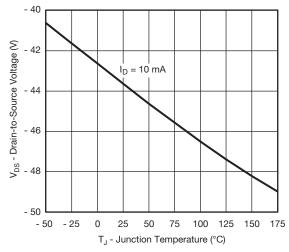
50 75 100 125



On-Resistance vs. Gate-to Source Voltage



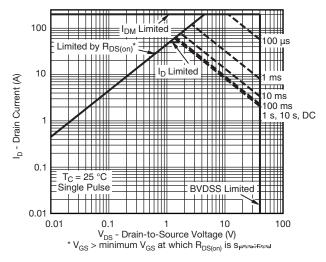
Transconductance



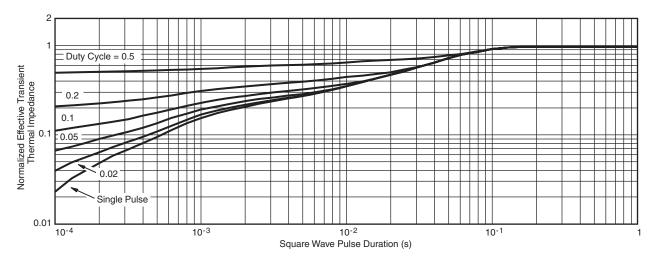
Drain Source Breakdown vs. Junction Temperature



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

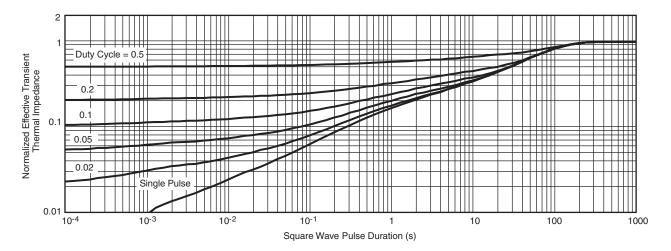


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case





Normalized Thermal Transient Impedance, Junction-to-Ambient

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265157.



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REVISION HISTORY a				
REVISION	DATE	DESCRIPTION OF CHANGE		
D	12-Dec-14	• I _D and P _D (T _C = 125 °C), UIS, R _{thJC} , R _{DS(on)} (V _{GS} = 10 V for T _J = 125 °C and 175 °C) and g _{fs} modified		

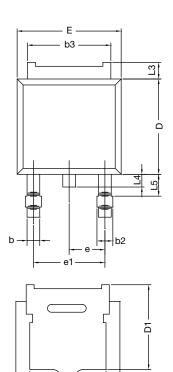
Note

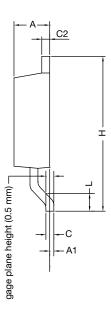
a. As of April 2014



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TO-252AA Case Outline





	MILLIN	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

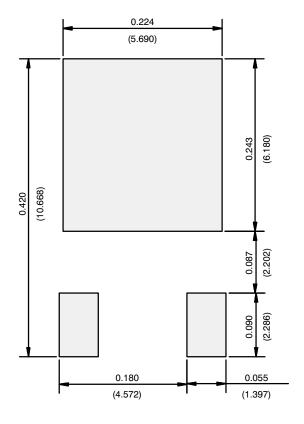
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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